

INFORMATION DISCLOSURE CITATION IN AN APPLICATION (PTO-1449)				ATTY. DOCKET NO. 60188-776		SERIAL NO.		
				APPLICANT Masao SHINDO				
				FILING DATE February 20, 2004		GROUP		
U.S. PATENT DOCUMENTS								
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear			
		US 5,856,003	01/05/1999	Chiu	_____			
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FOREIGN PATENT DOCUMENTS								
EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Code ¹ -Number & -Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation		
		JP 59-50227	12/07/1984	TOSHIBA CORP		Yes	No	
		JP P2001-291781A	10/19/2001	MATSUSHITA ELECTRIC IND CO LTD		(Japan w/English Abstract)		
						(Japan w/English Abstract)		
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)								
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.						
		Don H. LEE, et al., "Ion-Implanted Semiconductor Devices", Proceedings of the IEEE, pp.1241-1255, September 1974						
		EXAMINER				DATE CONSIDERED		

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